

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE40H12 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =40V,I_D =120A

 $R_{DS(ON)}$ <4 m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ <7.5m Ω @ V_{GS} =4.5V

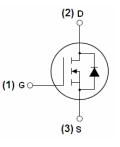
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H12	NCE40H12	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	120	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	85	Α
Pulsed Drain Current	I _{DM}	330	Α
Maximum Power Dissipation	P _D	130	W
Derating factor		0.8	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1080	mJ



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Operating Junction and Storage Temperature Range	T_J, T_STG	-55 To 175	$^{\circ}\! \mathbb{C}$
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Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	$R_{ heta JC}$	1.25	°C/W	
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics			•			•	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	45	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	<u>.</u>						
Gate Threshold Voltage	V _{GS(th)}	V_{DS} = V_{GS} , I_D =250 μ A	1.2	1.9	2.5	V	
Drain Course On State Begintenes	Б	V _{GS} =10V, I _D =20A	-	3.2	4.0	m=0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =10A	-	5.5	7.5	mΩ	
Forward Transconductance	g fs	V _{DS} =10V,I _D =20A	26	-	-	S	
Dynamic Characteristics (Note4)			•			•	
Input Capacitance	C _{lss}	V 00V/V 0V/	-	5400	-	PF	
Output Capacitance	C _{oss}	V_{DS} =20V, V_{GS} =0V, F=1.0MHz	-	970	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	380	-	PF	
Switching Characteristics (Note 4)			•			•	
Turn-on Delay Time	t _{d(on)}		-	15	-	nS	
Turn-on Rise Time	t _r	V_{DD} =20V, I_D =2A, R_L =1 Ω	-	18	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	52	-	nS	
Turn-Off Fall Time	t _f		-	23	-	nS	
Total Gate Charge	Qg	V 00V/1 00A	-	75		nC	
Gate-Source Charge	Q _{gs}	V _{DS} =20V,I _D =20A,	-	10.5		nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	17		nC	
Drain-Source Diode Characteristics	1		•	l .			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =10A	-		1.2	V	
Diode Forward Current (Note 2)	Is		-	-	120	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	42	-	nS	
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	45	-	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negli	gible (turi	n-on is do	ominated b	y LS+LD)	

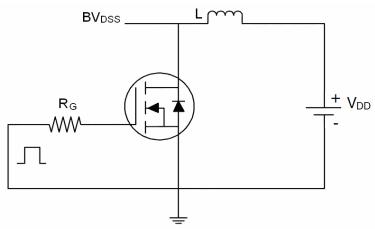
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production
- **5.** E_{AS} condition : Tj=25 $^{\circ}$ C,V_{DD}=20V,V_G=10V,L=1mH,Rg=25 Ω , I_{AS}=46.5A

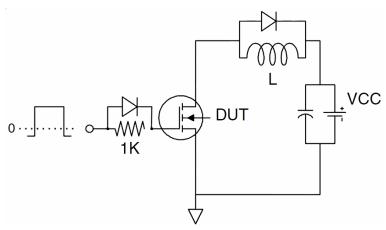


Test circuit

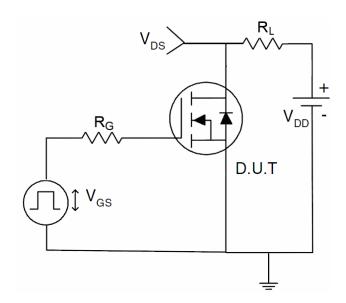
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

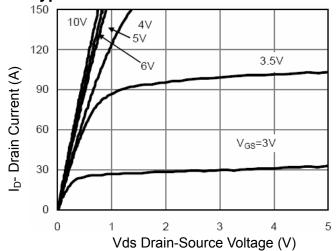


Figure 1 Output Characteristics

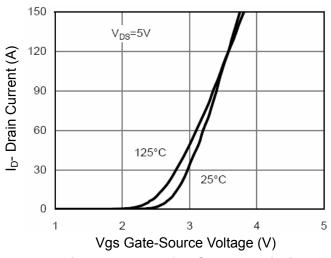


Figure 2 Transfer Characteristics

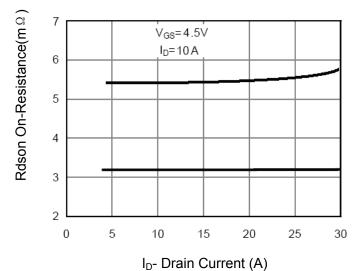


Figure 3 Rdson- Drain Current

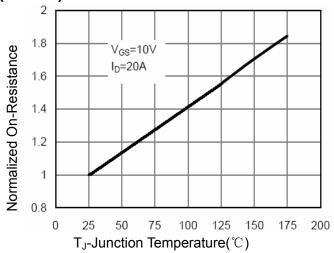


Figure 4 Rdson-JunctionTemperature

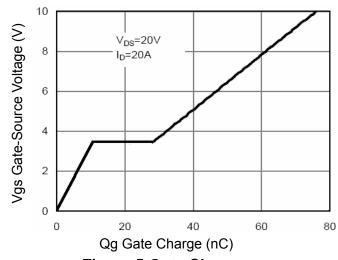


Figure 5 Gate Charge

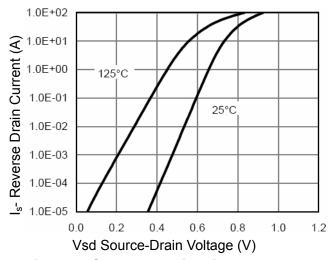
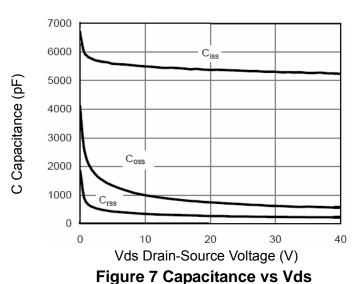
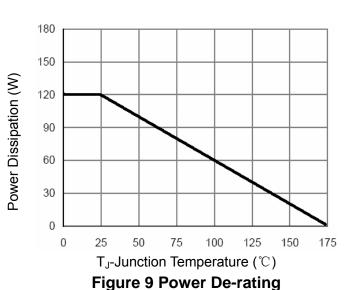


Figure 6 Source- Drain Diode Forward







1000.0

100.0

RDS(ON)

Imited

100 DC

100 DC

100 DC

10ms

Figure 8 Safe Operation Area

Vds Drain-Source Voltage (V)

V_{cs}(th) (norm)
1.0
0.9
0.8
0.7
0.6
-50 0 50 100 T_J(°C)
T_J-Junction Temperature(°C)

Figure 10 $V_{GS(th)}$ vs Junction Temperature



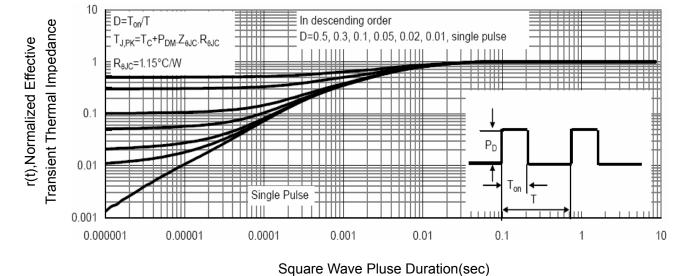
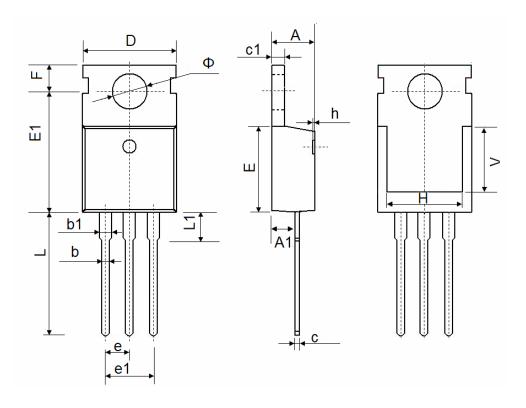


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



Cumbal	Dimensions I	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	V 7.500 REF.		0.295	REF.	
Ф	3.400	3.800	0.134	0.150	



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Pb Free Product
NCE40H12

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